

NEW PRODUCT

**Product Summary**

$V_{(BR)DSS}$	$R_{DS(ON)}$ max	$I_D$ max $T_A = +25^\circ C$
-30V	65mΩ @ $V_{GS} = -10V$	-3.8A
	99mΩ @ $V_{GS} = -4.5V$	-3.0A

**Description**

This MOSFET has been designed to minimize the on-state resistance ( $R_{DS(ON)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

**Applications**

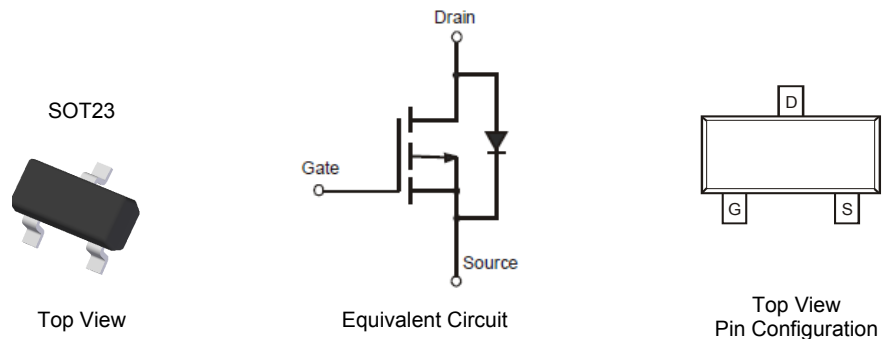
- Backlighting
- Power Management Functions
- DC-DC Converters

**Features and Benefits**

- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

**Mechanical Data**

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208  $\text{e3}$
- Terminal Connections: See Diagram
- Weight: 0.008 grams (approximate)

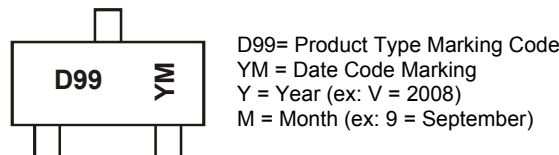


**Ordering Information** (Note 4)

Part Number	Compliance	Case	Packaging
DMP3099L-7	Standard	SOT23	3000/Tape & Reel
DMP3099L-13	Standard	SOT23	10000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

**Marking Information**



Date Code Key

Year	2008	2009	2010	2011	2012	2013	2014	2015
Code	V	W	X	Y	Z	A	B	C

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V <sub>DSS</sub>	-30	V
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
Drain Current (Note 5) V <sub>GS</sub> = -10V	Steady State	T <sub>A</sub> = +25°C	I <sub>D</sub>	-3.8	A
		T <sub>A</sub> = +70°C		-2.9	
Pulsed Drain Current (Note 6)			I <sub>DM</sub>	-11	A

**Thermal Characteristics**

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	P <sub>D</sub>	1.08	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°C (Note 5)	R <sub>θJA</sub>	115	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-30	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	-800	nA	V <sub>DS</sub> = -30V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	-1.0	—	-2.1	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA
Static Drain-Source On-Resistance	R <sub>DS(on)</sub>	—	—	65	mΩ	V <sub>GS</sub> = -10V, I <sub>D</sub> = -3.8A
				99		V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -3.0A
Forward Transfer Admittance	Y <sub>fs</sub>	—	3.6	—	S	V <sub>DS</sub> = -5V, I <sub>D</sub> = -2.7A
Diode Forward Voltage (Note 6)	V <sub>SD</sub>	—	—	-1.26	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -2.7A
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	C <sub>iss</sub>	—	563	—	pF	V <sub>DS</sub> = -25V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	48	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	41	—	pF	
Gate Resistance	R <sub>G</sub>	—	10.3	—	Ω	V <sub>GS</sub> = 0V V <sub>DS</sub> = 0V, f = 1MHz
<b>SWITCHING CHARACTERISTICS (Note 8)</b>						
Total Gate Charge	Q <sub>g</sub>	—	5.2	—	nC	V <sub>DS</sub> = -15V, V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -3.8A
			11			
			1.7			
Gate-Source Charge	Q <sub>gs</sub>	—	1.7	—	ns	V <sub>DS</sub> = -15V, V <sub>GS</sub> = -10V, I <sub>D</sub> = -3.8A
Gate-Drain Charge	Q <sub>gd</sub>	—	1.9	—		
Turn-On Delay Time	t <sub>d(on)</sub>	—	4.8	—	ns	V <sub>DS</sub> = -15V, V <sub>GS</sub> = -10V, I <sub>D</sub> = -1A, R <sub>G</sub> = 6.0Ω
Rise Time	t <sub>r</sub>	—	5.0	—		
Turn-Off Delay Time	t <sub>d(off)</sub>	—	31	—		
Fall Time	t <sub>f</sub>	—	15	—		

- Notes:
- Device mounted on FR-4 PCB on 2 oz., 0.5 in.<sup>2</sup> copper pads and t ≤ 5 sec.
  - Pulse width ≤ 10μs, Duty Cycle ≤ 1%.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to production testing.

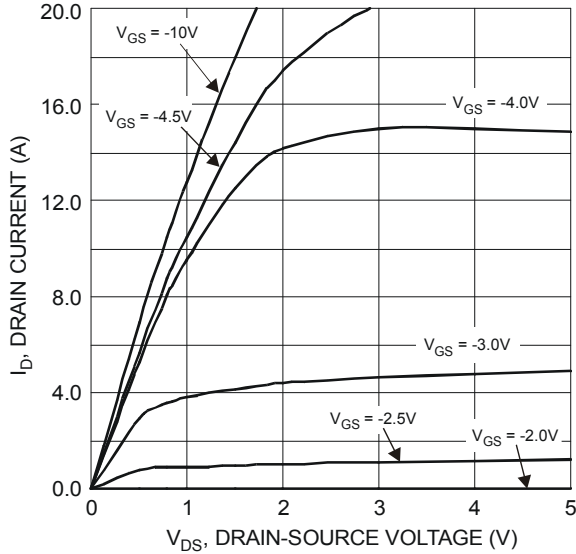


Figure 1 Typical Output Characteristics

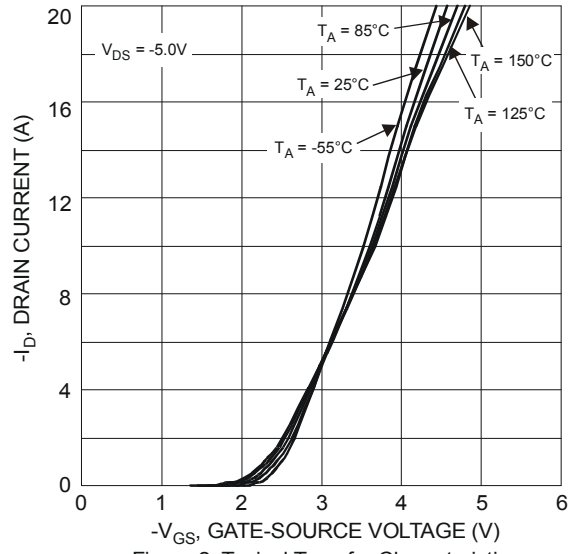


Figure 2 Typical Transfer Characteristics

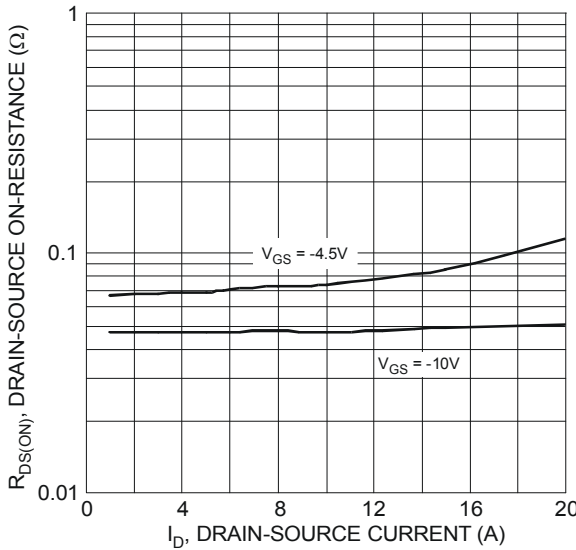


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

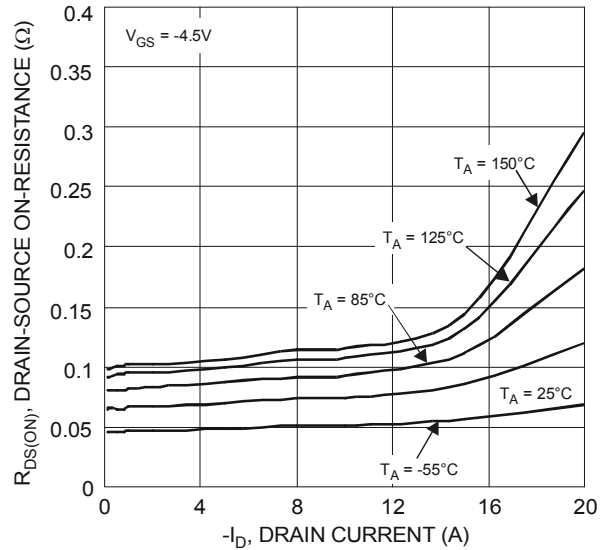


Figure 4 Typical On-Resistance vs. Drain Current and Temperature

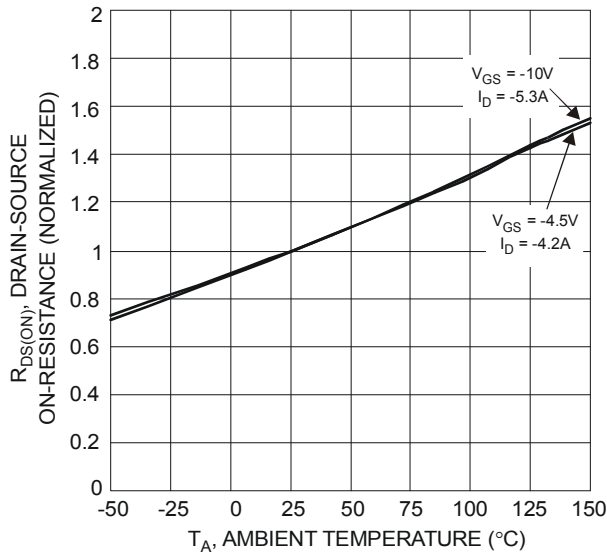


Figure 5 On-Resistance Variation with Temperature

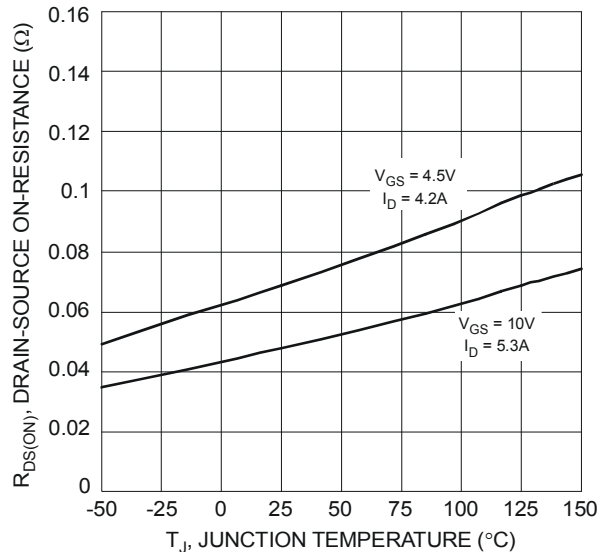


Figure 6 On-Resistance Variation with Temperature

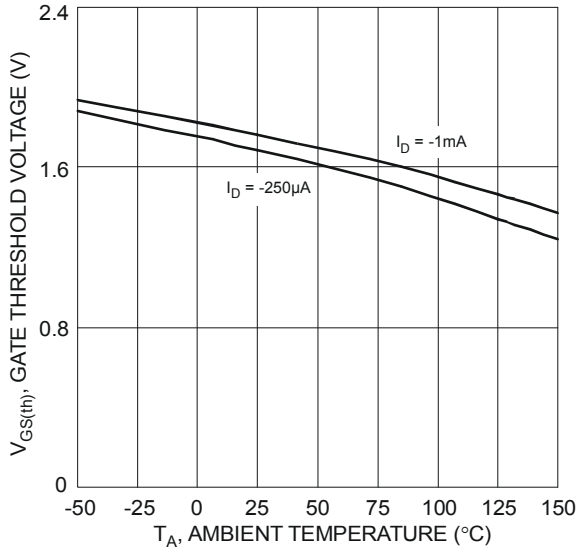


Figure 7 Gate Threshold Variation vs. Ambient Temperature

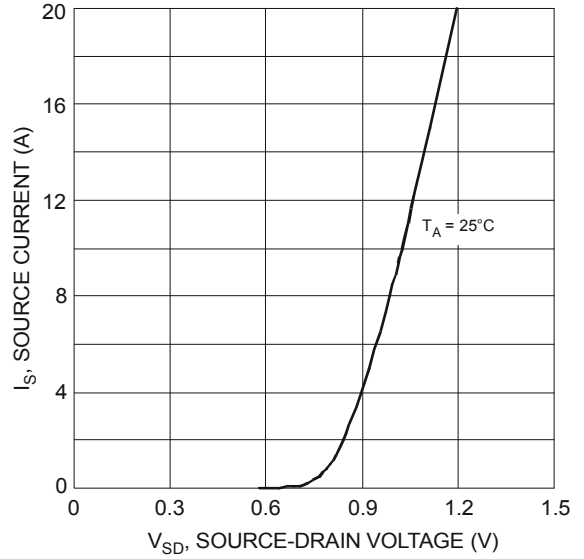


Figure 8 Diode Forward Voltage vs. Current

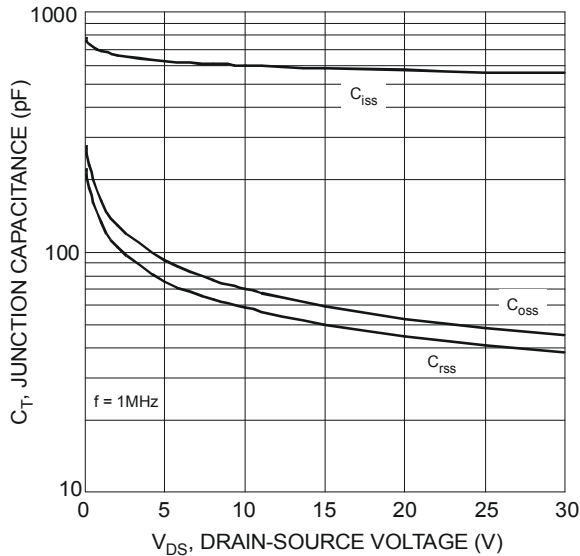


Figure 9 Typical Junction Capacitance

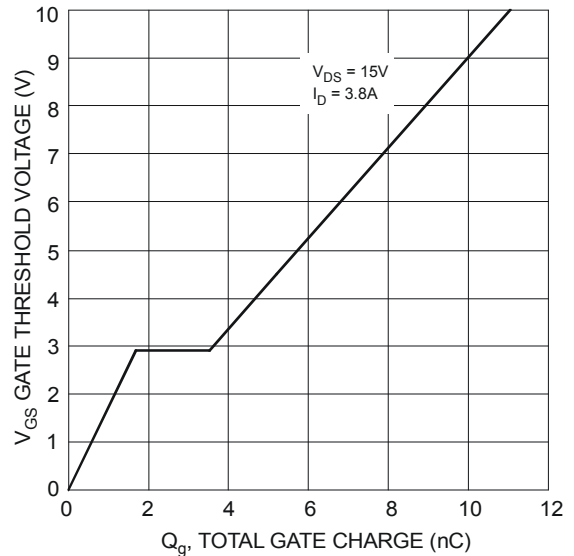
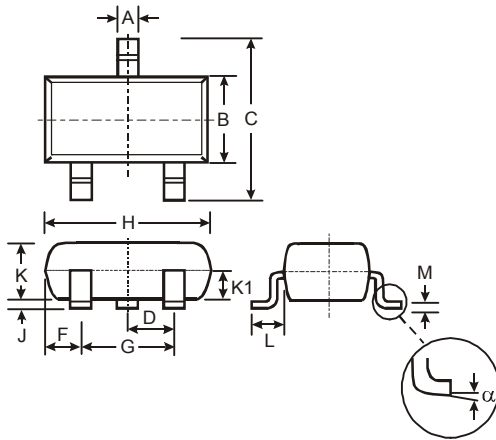


Figure 10 Gate Charge

**Package Outline Dimensions**

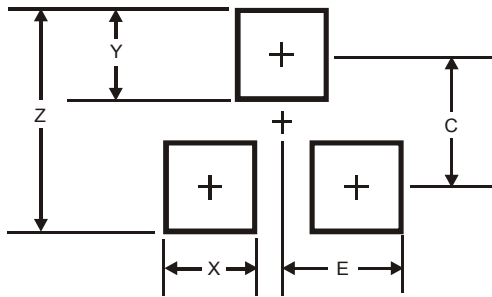
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.903	1.10	1.00
K1	-	-	0.400
L	0.45	0.61	0.55
M	0.085	0.18	0.11
α	0°	8°	-
All Dimensions in mm			

**Suggested Pad Layout**

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35

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